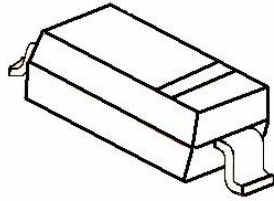


SOD323



Marking: S9

SOD-323 贴片塑封肖特基二极管 SOD-323 Plastic-Encapsulate Schottky Barrier Diode

特征 Features

- 大电流承受能力。High Current Capability
- 正向压降低。Low Forward Voltage Drop

机械数据 Mechanical Data

- 封装: SOD-323 封装 SOD-323 Small Outline Plastic Package
- 极性: 色环端为负极 Polarity: Color band denotes cathode end
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	界限 Limit	单位 Unit
最大可重复峰值反向电压 Maximum repetitive peak reverse voltage	VRRM	100	V
最大正向平均整流电流 Maximum average forward rectified current	IFM	350	mA
峰值正向浪涌电流 8.3ms 单一正弦半波 Peak forward surge current 8.3 ms single half sine-wave	IFSM	750	mA
典型热阻 Typical thermal resistance	RθJA	500	°C/W
功率消耗 Power Dissipation	PD	200	mW
Junction temperature 结温	Tj	125	°C
存储温度 Storage temperature range	TSTG	-55-+150	°C

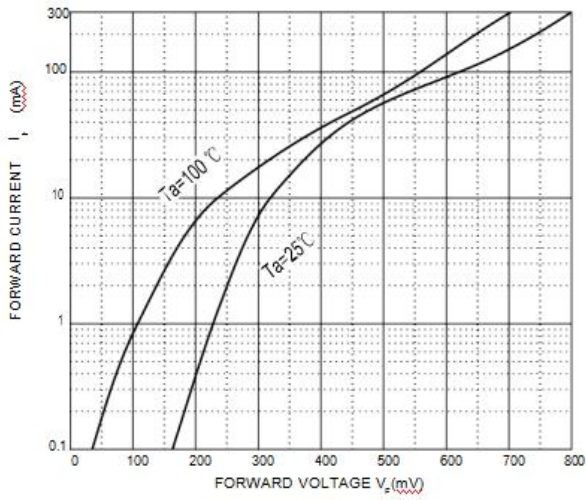
电特性 (TA = 25°C 除非另有规定)

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

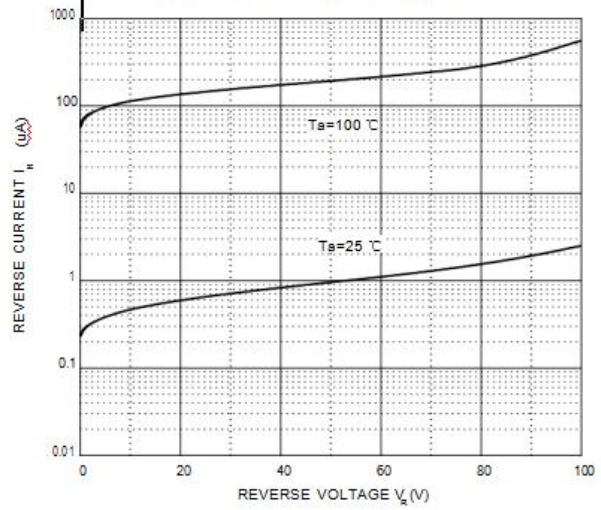
参数 Parameters	符号 Symbol	测试条件 Test conditions	Min	Typ	Max	单位 Unit
最大正向电压 Maximum forward voltage	VF1	IF = 0.1mA			250	mV
	VF2	IF = 10mA			450	
	VF3	IF = 250mA			1000	
最大反向电压 Maximum reverse breakdown voltage	VR	IR=100uA	100			V
最大反向电流 Maximum reverse current	IR	VR1=1.5V			0.3	uA
		VR2=10V			0.5	
		VR3=50V			1.0	
		VR4=75V			2.0	
典型结电容 Type junction capacitance	CT	VR = 0V, f = 1MHz		20		pF
		VR = 1V, f = 1MHz		12		

Typical Characteristics

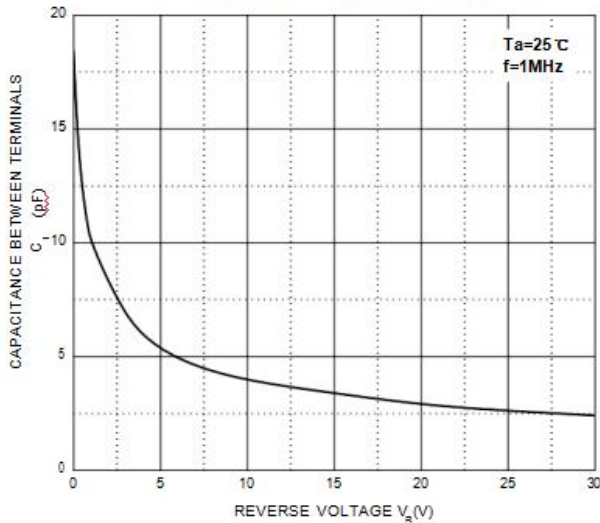
Forward Characteristics



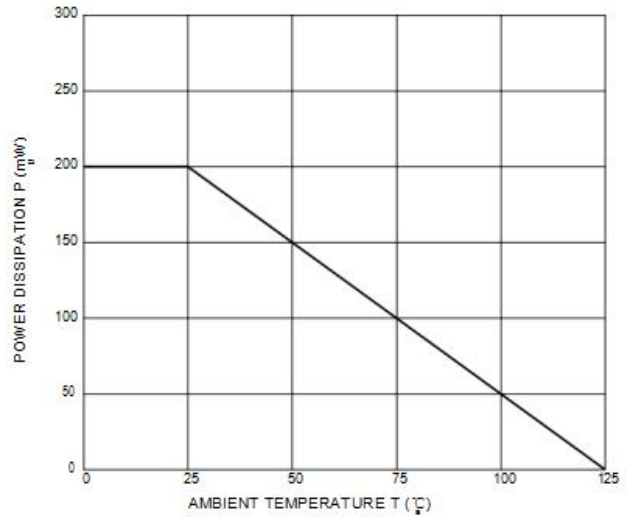
Reverse Characteristics



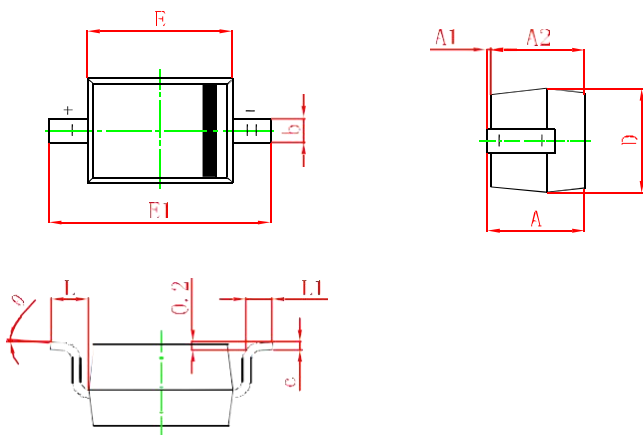
Capacitance Characteristics



Power Derating Curve



SOD-323 PACKAGE OUTLINE Plastic surface mounted package



Symbol	Min.(mm)	Max.(mm)
A		1.000
A1	0.000	0.100
A2	0.800	0.900
b	0.250	0.350
c	0.080	0.150
D	1.200	1.400
E	1.600	1.800
E1	2.500	2.700
L	0.475REF	
L1	0.250	0.400
θ	0°	8°